



# THE DATASHEET OF ZVP3310A



# ZVP3310A

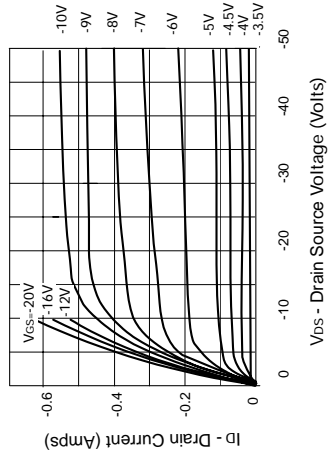
## P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 – MARCH 94

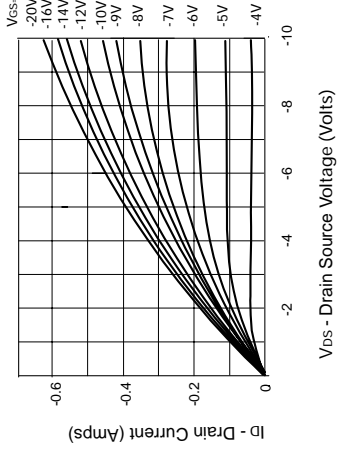
### FEATURES

- \* 100 Volt  $V_{DS}$
- \*  $R_{DS(on)}=20\Omega$

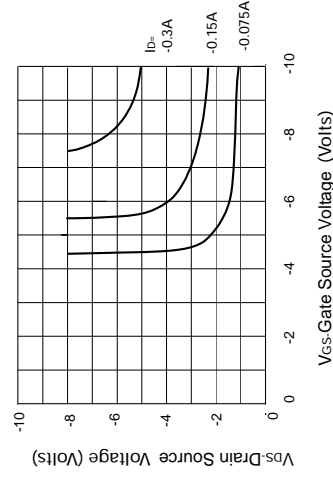
### TYPICAL CHARACTERISTICS



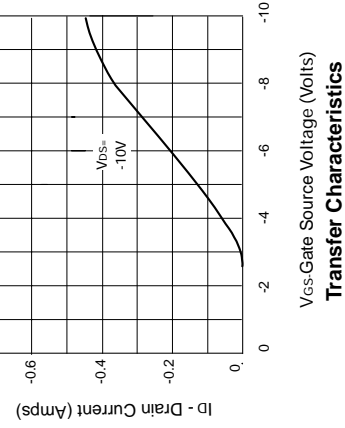
**Output Characteristics**



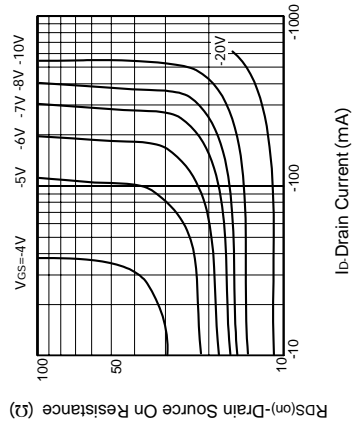
**Saturation Characteristics**



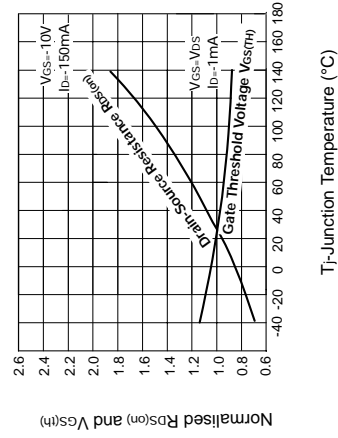
**Voltage Saturation Characteristics**



**Transfer Characteristics**



**On-resistance v drain current**



**Normalised RDS(on) and VGS(th) v Temperature**

3-433

Switching times measured with 50Ω source

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL
Drain-Source Voltage	$BV_{DSS}$
Continuous Drain Current at $T_{amb}=25^{\circ}C$	$I_{D(on)}$
Pulsed Drain Current	$R_{DS(on)}$
Gate Source Voltage	$I_{D(on)}$
Power Dissipation at $T_{amb}=25^{\circ}C$	$R_{DS(on)}$
Operating and Storage Temperature Range	$I_{D(on)}$

### ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	$BV_{DSS}$
Gate-Source Threshold Voltage	$V_{GS(th)}$
Gate-Body Leakage	$I_{GSS}$
Zero Gate Voltage Drain Current	$I_{DSS}$
On-State Drain Current(1)	$I_{D(on)}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$
Forward Transconductance (1)(2)	$g_{fs}$
Input Capacitance (2)	$C_{iss}$
Common Source Output Capacitance (2)	$C_{oss}$
Reverse Transfer Capacitance (2)	$C_{riss}$
Turn-On Delay Time (2)(3)	$t_{d(on)}$
Rise Time (2)(3)	$t_r$
Turn-Off Delay Time (2)(3)	$t_{d(off)}$
Fall Time (2)(3)	$t_f$

(1) Measured under pulsed conditions. Wire (2) Sample test.

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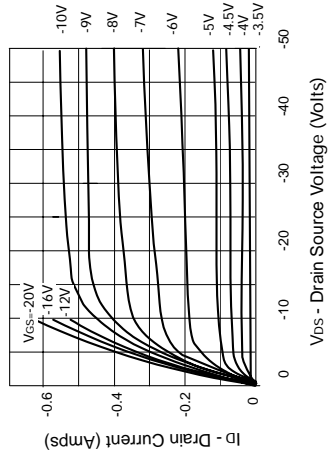
## P-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

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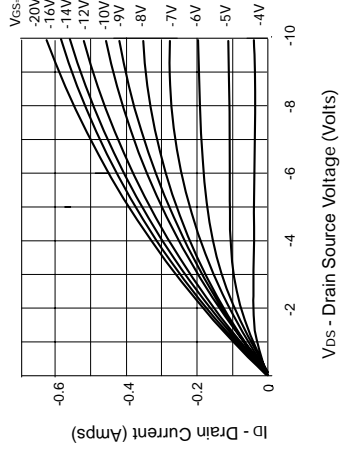
### FEATURES

- \* 100 Volt  $V_{DS}$
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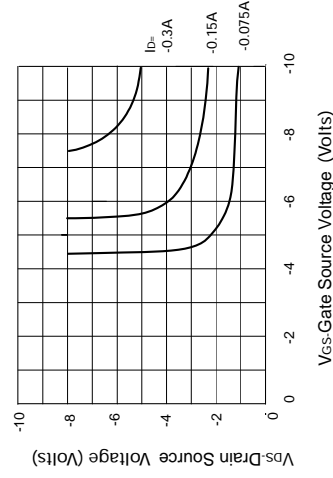
### TYPICAL CHARACTERISTICS



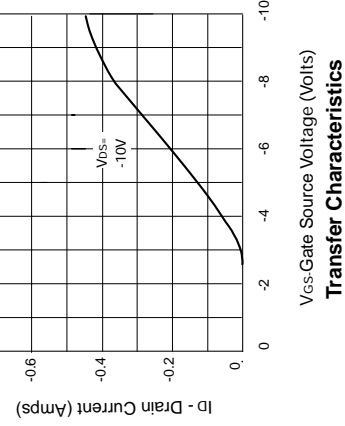
**Output Characteristics**



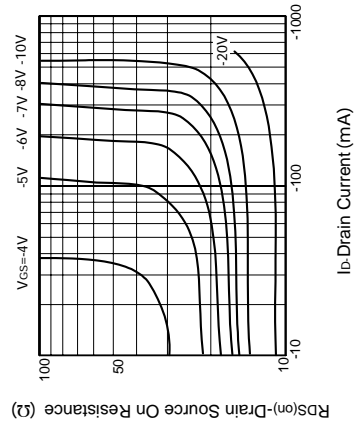
**Saturation Characteristics**



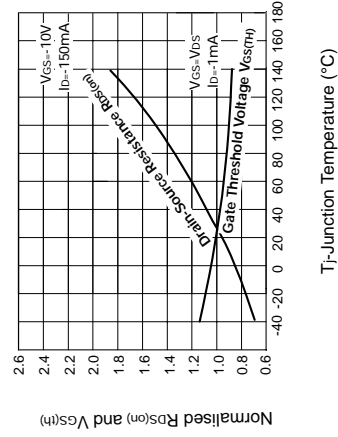
**Voltage Saturation Characteristics**



**Transfer Characteristics**



**On-resistance v drain current**



**Normalised RDS(on) and VGS(th) v Temperature**

3-433

### ABSOLUTE MAXIMUM RATINGS

PARAMETER	
Drain-Source Voltage	
Continuous Drain Current at $T_{amb}=25^{\circ}\text{C}$	
Pulsed Drain Current	
Gate Source Voltage	
Power Dissipation at $T_{amb}=25^{\circ}\text{C}$	
Operating and Storage Temperature Range	

### ELECTRICAL CHARACTERISTICS

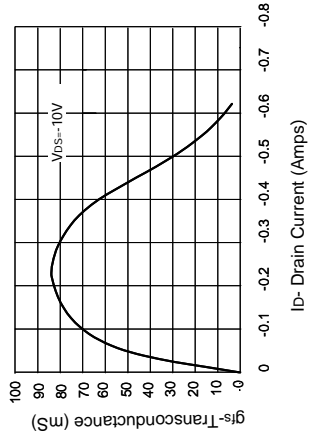
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Turn-On Delay Time (2)(3)	$t_{d(on)}$
Rise Time (2)(3)	$t_r$
Turn-Off Delay Time (2)(3)	$t_{d(off)}$
Fall Time (2)(3)	$t_f$

(1) Measured under pulsed conditions. Wire bonded.  
 (2) Sample test.

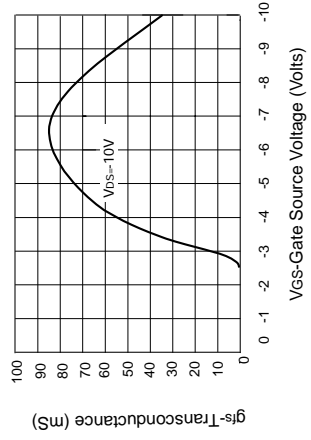
Switching times measured with 50Ω source

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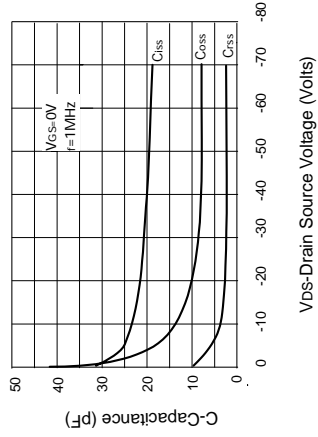
## TYPICAL CHARACTERISTICS



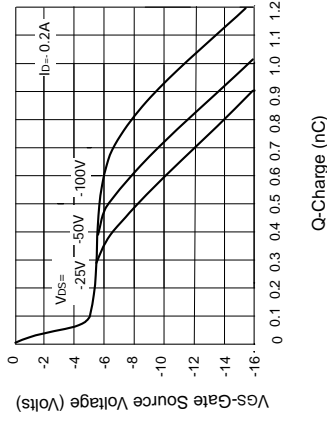
Transconductance v drain current



Transconductance v gate-source voltage



Capacitance v drain-source voltage



Gate charge v gate-source voltage

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